## **Amendments To The Claims**

The listing of claims presented below will replace all prior versions, and listings, of claims in the application.

## **Listing of claims:**

1. (original) An apparatus for generating a driving voltage for a sense amplifier in a memory device, the apparatus comprising:

voltage output means for outputting a predetermined value of voltage for driving the sense amplifier to a node being used as a driving voltage node of the sense amplifier;

a first core voltage step-up means connected between a power supply and the node; and

a second core voltage step-up means connected between the power supply and the node,

wherein the first and second core voltage step-up means are is turned on in sequence to elevate the voltage level of the node connected with the sense amplifier up to the level of the power supply at a first rate, and

wherein, any time after the first core voltage step-up means is initially turned on, the second core voltage step-up means is turned on to elevate the voltage level of the node up to the level of the power supply at a second rate.

2. (original) The apparatus as set forth in claim 1, wherein the first core voltage step-up means includes a first transistor, the second core voltage step-up

means includes a second transistor, the first core voltage step-up means is enabled in response to a bank active signal, and the second core voltage step-up means is enabled in response to a sense amplifier enable-signal.

- 3. (original) The apparatus as set forth in claim 2, wherein the first transistor is smaller-sized than the second transistor.
- 4. (original) The apparatus as set forth in claim 2, wherein the voltage output means are inoperative when the first core voltage step-up means is enabled.
- 5. (original) The apparatus as set forth in claim 1, wherein the voltage output means are arranged corresponding to each of banks in the memory device.
- 6. (new) The apparatus as set forth in claim 1, wherein the second rate is faster than the first rate.